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(54) **INTEGRATE RINSE MODULE IN HYBRID BONDING PLATFORM**

(71) Applicant: **Taiwan Semiconductor Manufacturing Company, Ltd.,**
Hsin-Chu (TW)

(72) Inventors: **Xin-Hua Huang**, Xihu Township (TW);
Ping-Yin Liu, Yonghe (TW);
Hung-Hua Lin, Taipei (TW);
Xin-Chung Kuang, Hsinchu (TW);
Yuan-Chih Hsieh, Hsin-Chu (TW);
Lan-Lin Chao, Sindian (TW);
Chia-Shiung Tsai, Hsin-Chu (TW);
Xiaomeng Chen, Hsin-Chu (TW)

(73) Assignee: **Taiwan Semiconductor Manufacturing Company, Ltd.,**
Hsin-Chu (TW)

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B23K 1/00 (2006.01)
B23K 20/02 (2006.01)
B23K 20/233 (2006.01)
B23K 20/24 (2006.01)

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USPC 228/122.1, 123.1, 124.1, 124.5, 178, 228/179.1
See application file for complete search history.

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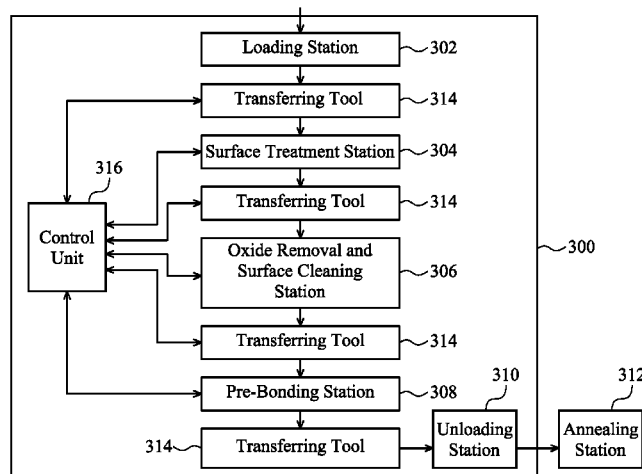
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Primary Examiner — Erin Saad
(74) *Attorney, Agent, or Firm* — Slater Matsil, LLP

(57) **ABSTRACT**
A method includes performing a plasma activation on a surface of a first package component, removing oxide regions from surfaces of metal pads of the first package component, and performing a pre-bonding to bond the first package component to a second package component.

19 Claims, 10 Drawing Sheets



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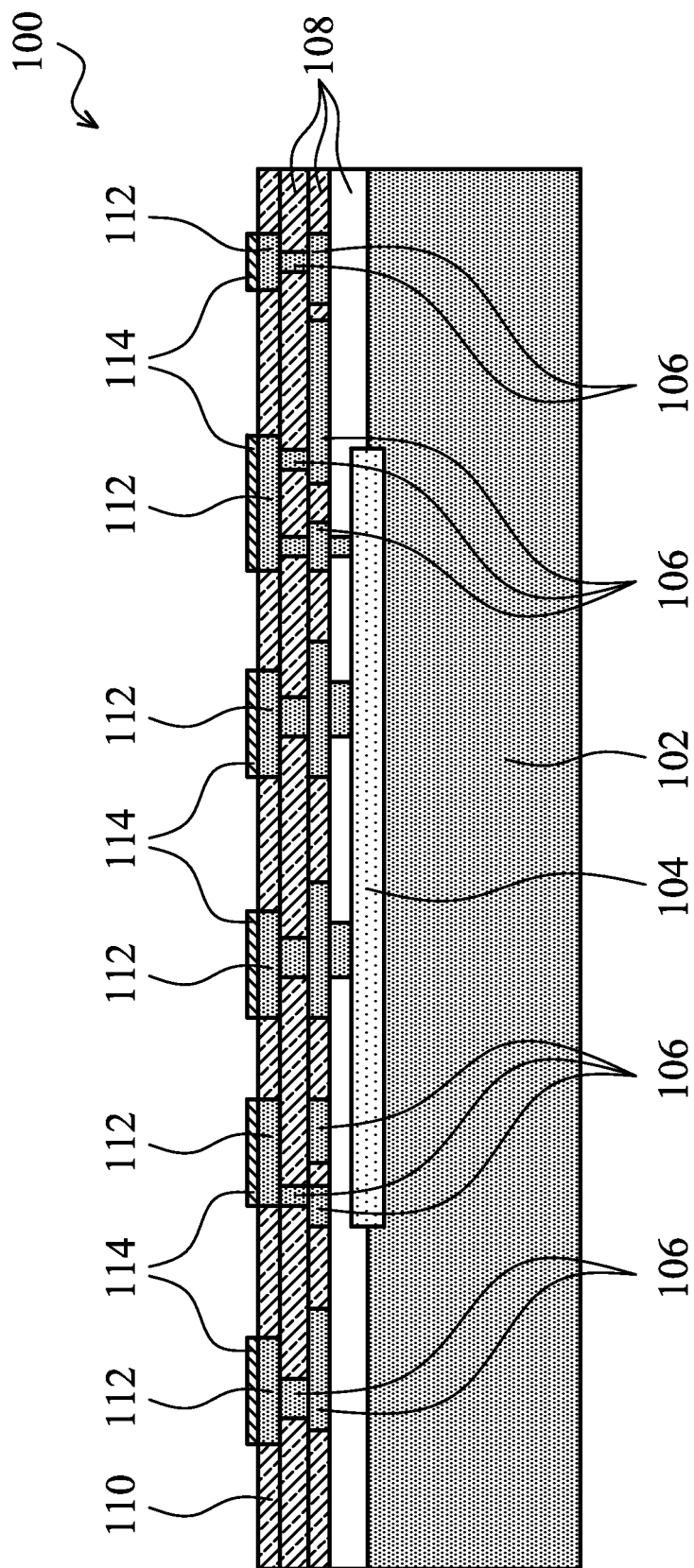


Fig. 1

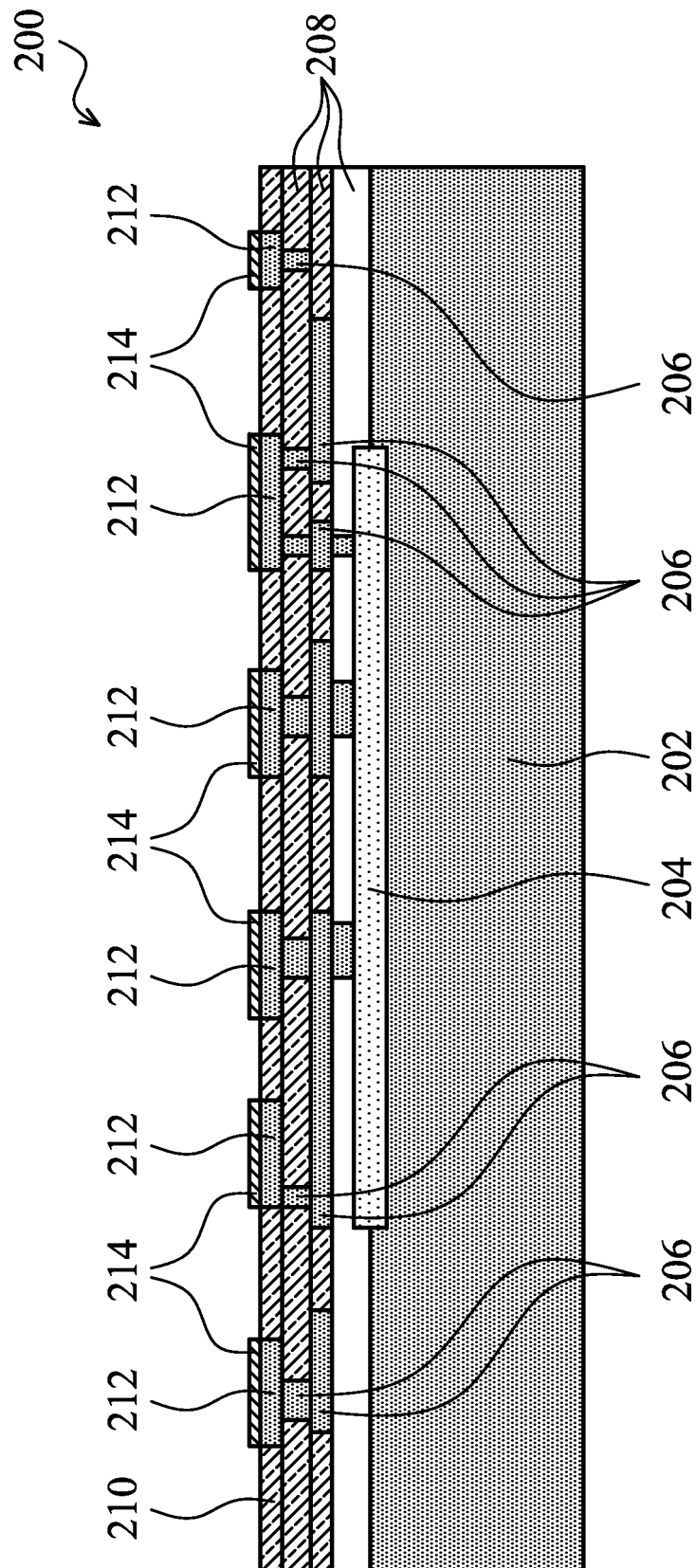


Fig. 2

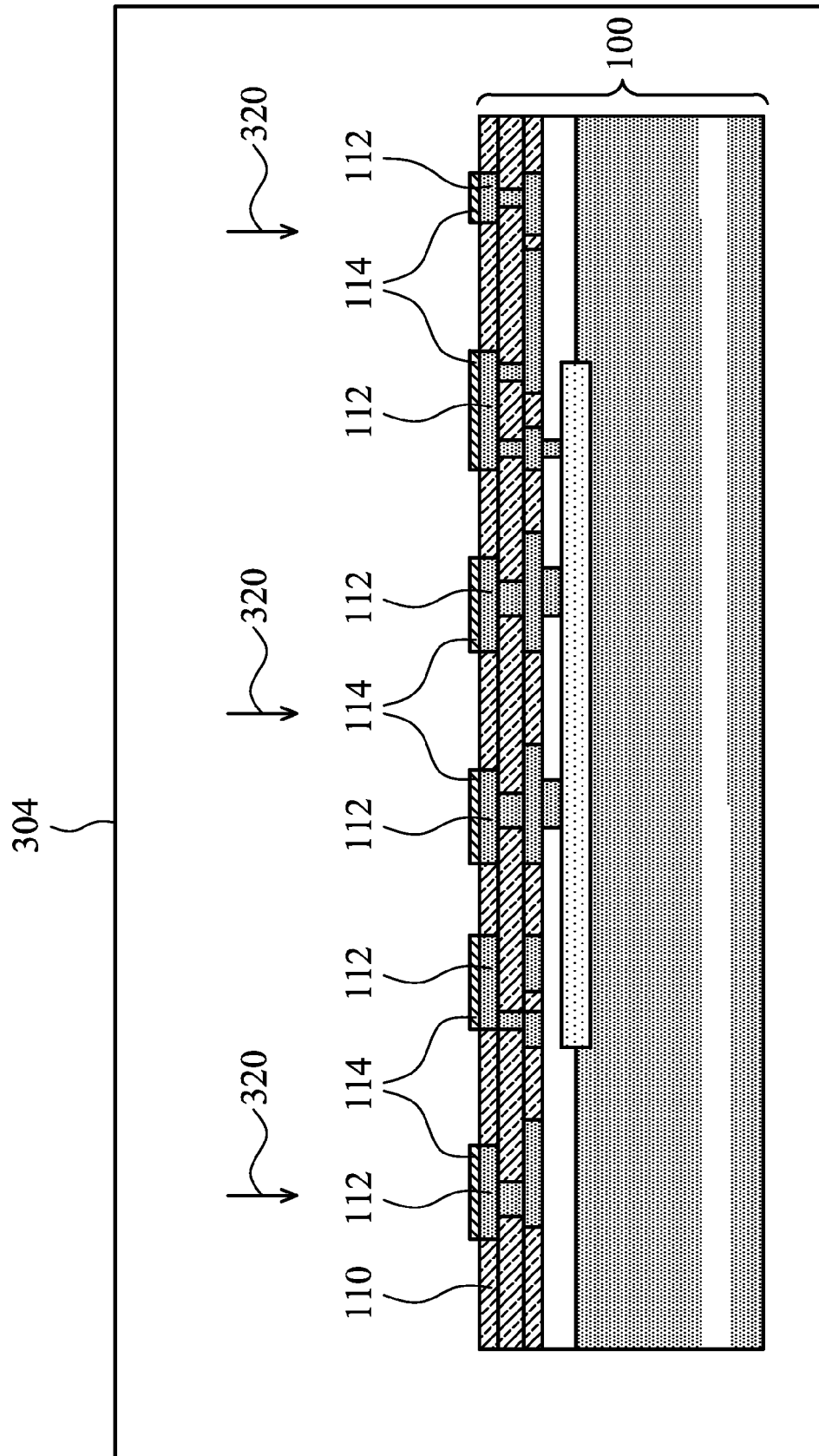
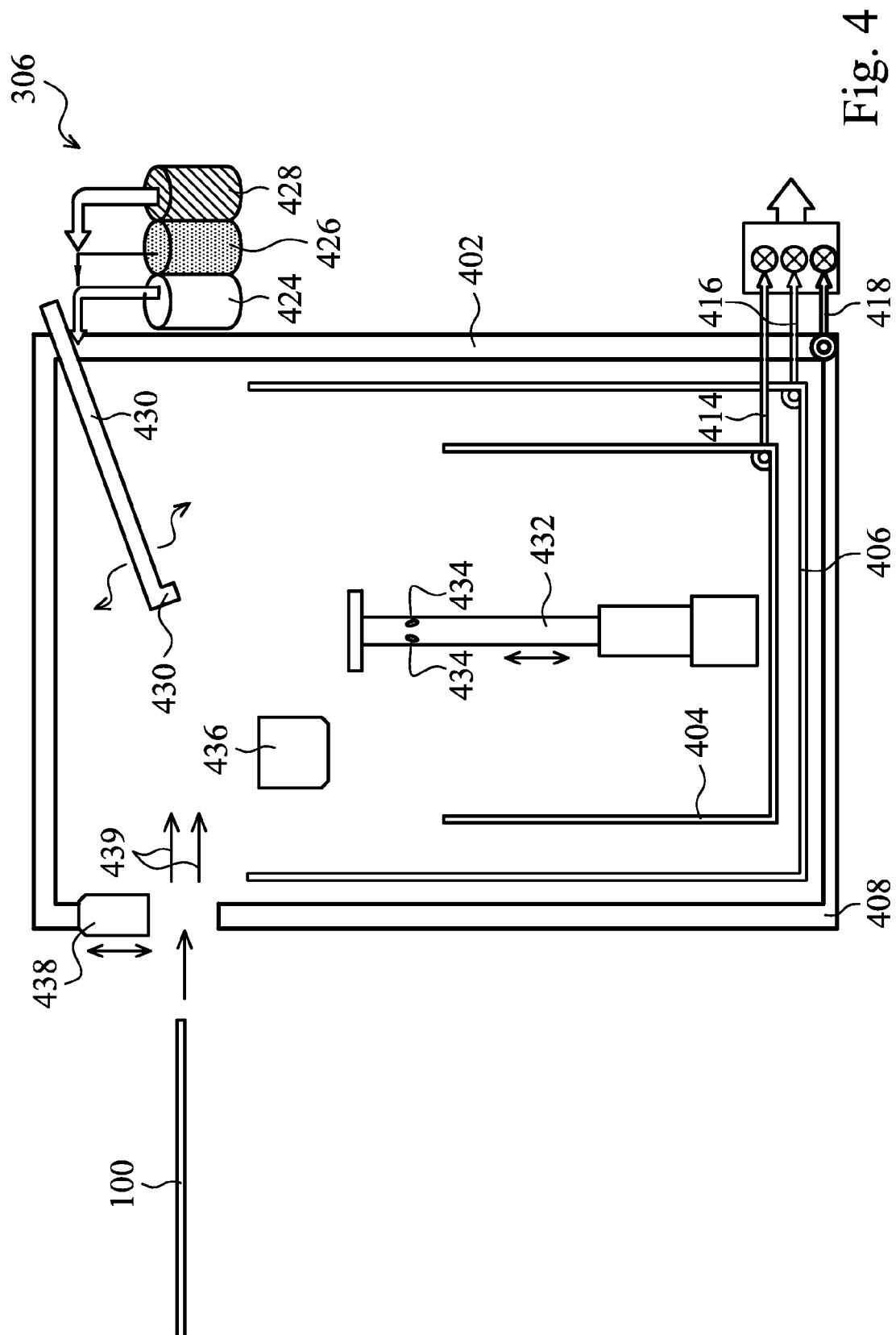


Fig. 3



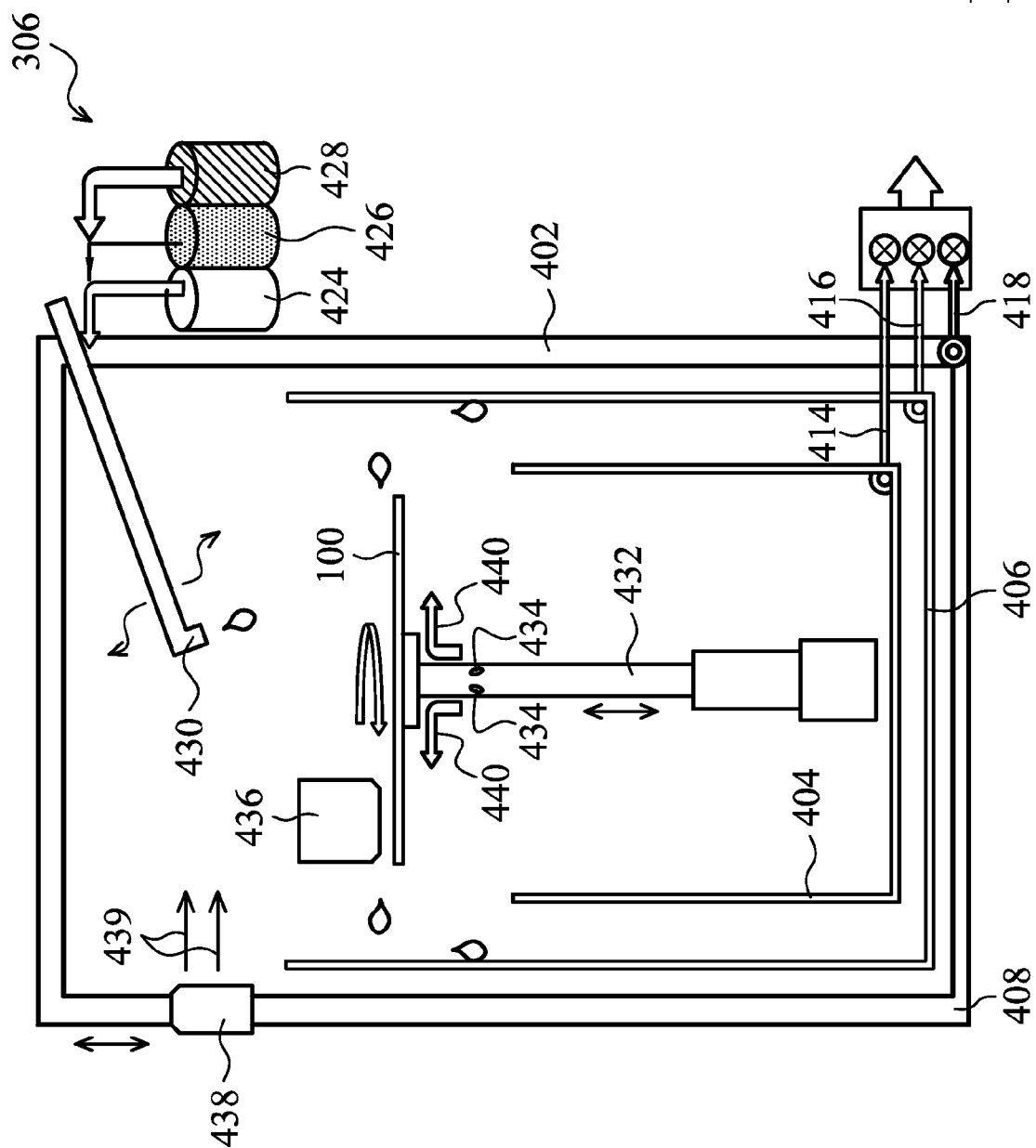


Fig. 5A

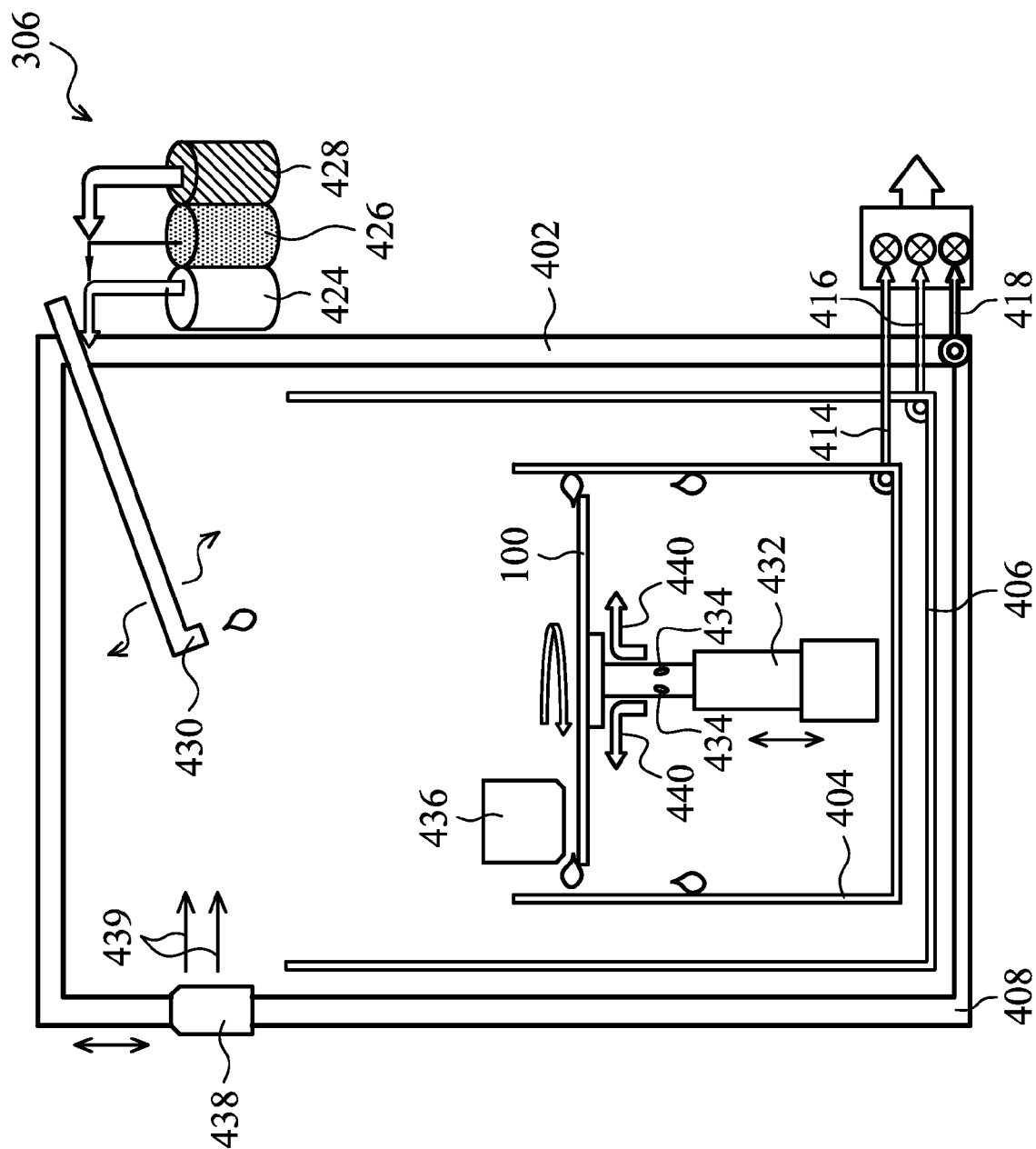


Fig. 5B

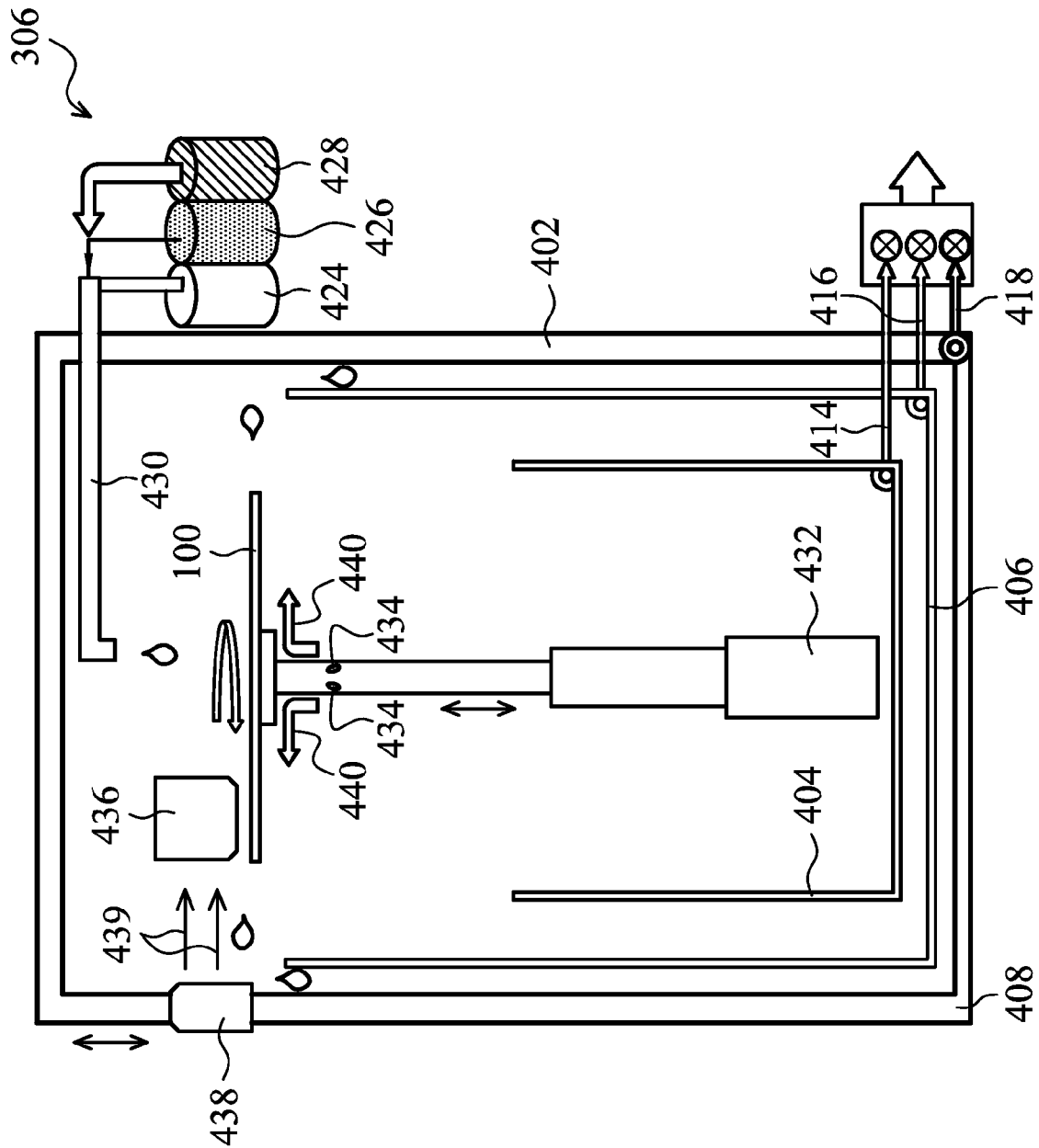


Fig. 6

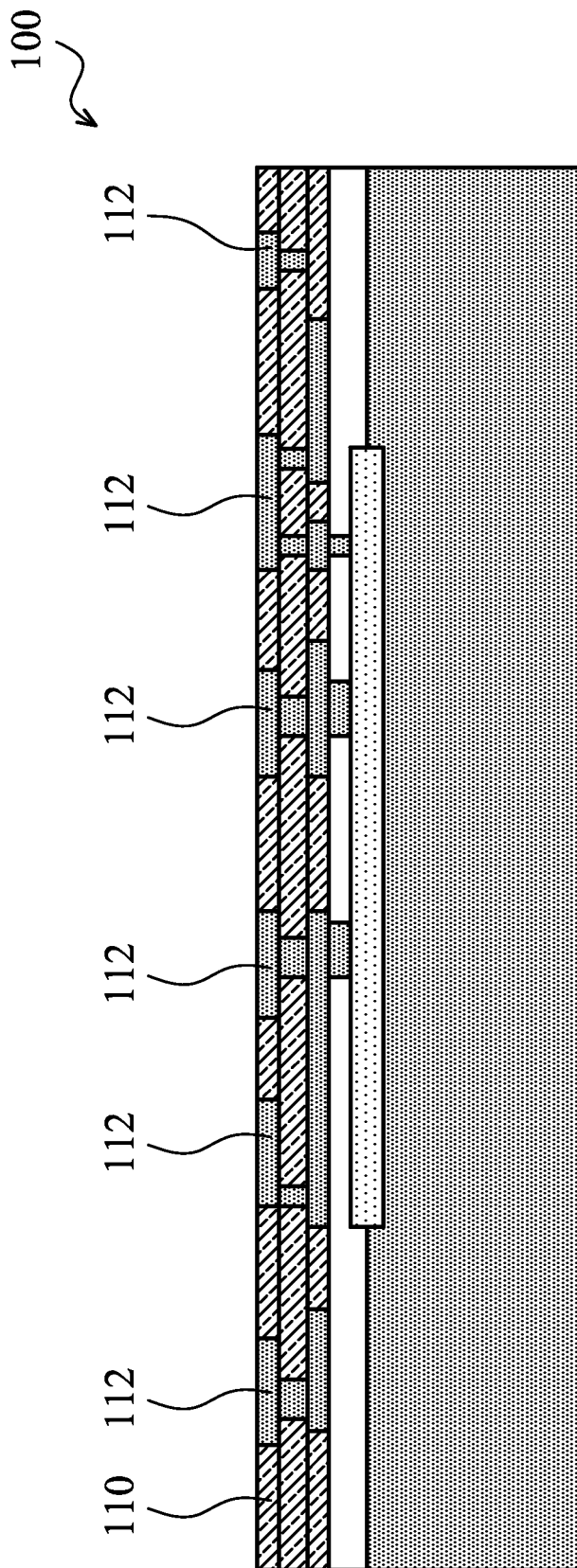


Fig. 7

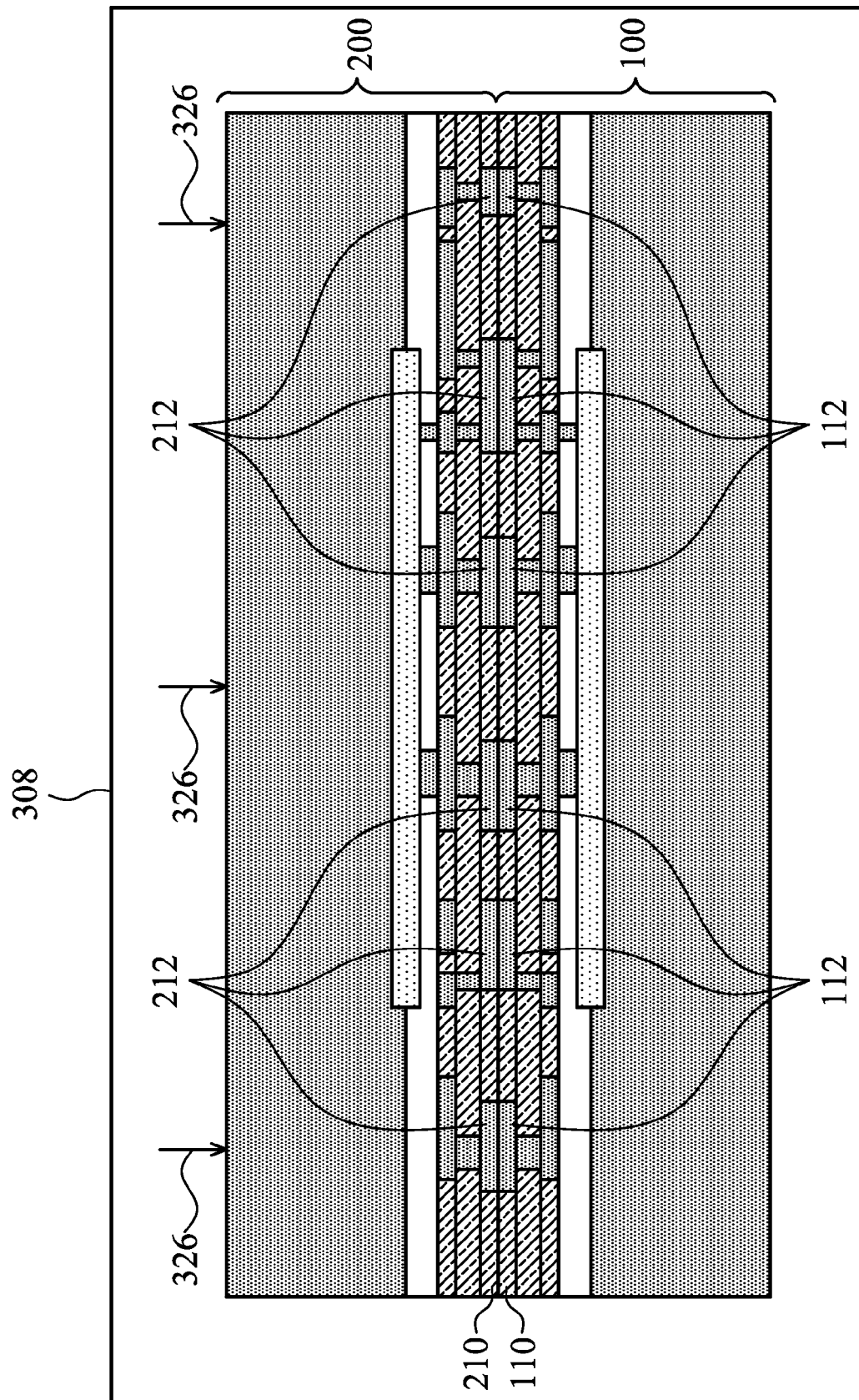


Fig. 8

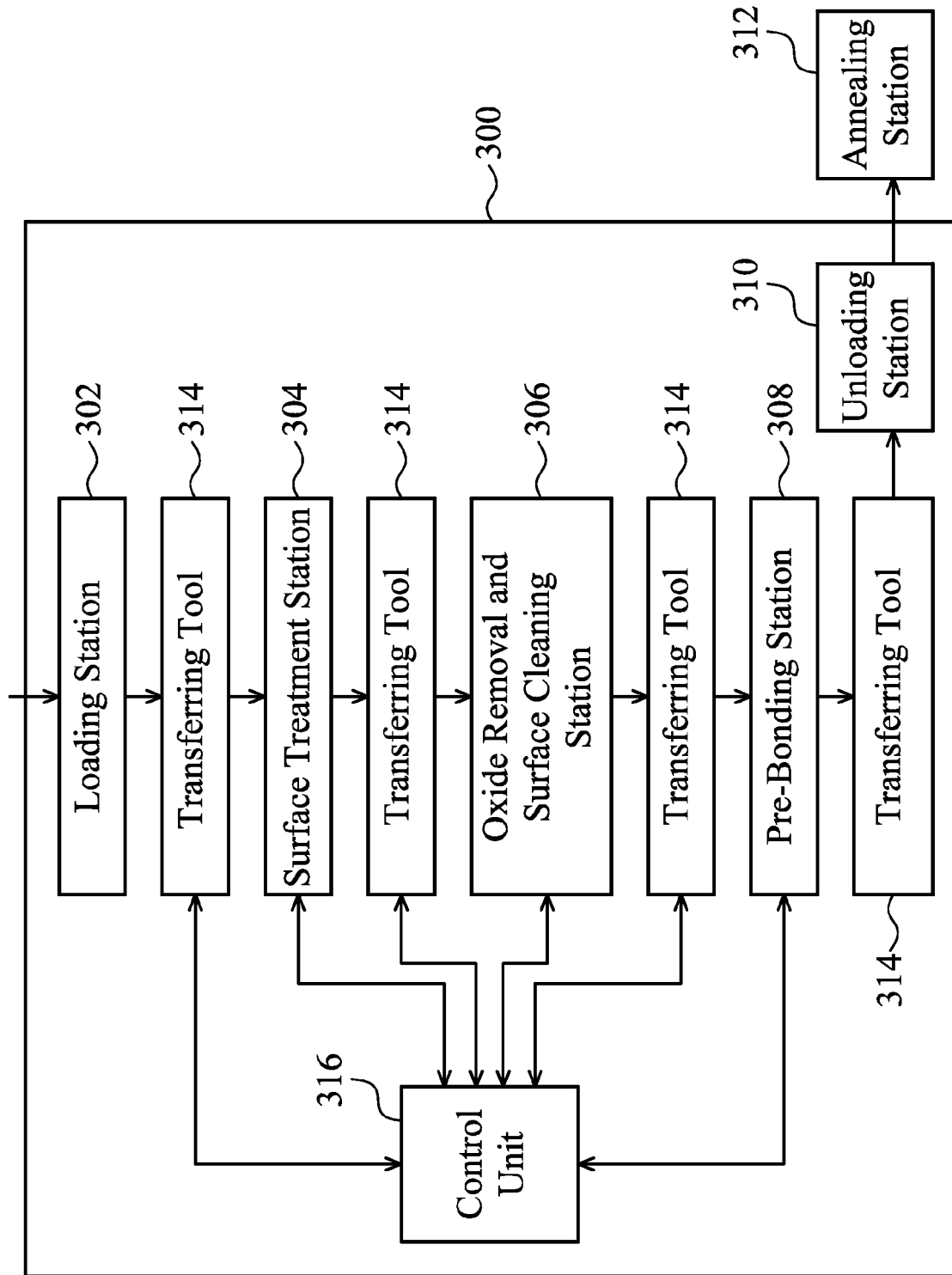


Fig. 9

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INTEGRATE RINSE MODULE IN HYBRID BONDING PLATFORM

This application claims the benefit of the following provisionally filed U.S. patent application: Application Ser. No. 61/785,993, filed Mar. 14, 2013, and entitled "Integrated Clean Station in Hybrid Bonding System," which application is hereby incorporated herein by reference.

BACKGROUND

In wafer-to-wafer bonding technology, various methods have been developed to bond two package components (such as wafers) together. The available bonding methods include fusion bonding, eutectic bonding, direct metal bonding, hybrid bonding, and the like. In the fusion bonding, an oxide surface of a wafer is bonded to an oxide surface or a silicon surface of another wafer. In the eutectic bonding, two eutectic materials are placed together, and are applied with a high pressure and a high temperature. The eutectic materials are hence melted. When the melted eutectic materials are solidified, the wafers are bonded together. In the direct metal-to-metal bonding, two metal pads are pressed against each other at an elevated temperature, and the inter-diffusion of the metal pads causes the bonding of the metal pads. In the hybrid bonding, the metal pads of two wafers are bonded to each other through direct metal-to-metal bonding, and an oxide surface of one of the two wafers is bonded to an oxide surface or a silicon surface of the other wafer.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the embodiments, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

FIG. 1 illustrates a schematic cross-sectional view of a first package component that is to be bonded in accordance with some exemplary embodiments;

FIG. 2 illustrates a schematic cross-sectional view of a second package component that is to be bonded to the first package component;

FIG. 3 illustrates a cross-sectional view of a plasma activation of the first package component;

FIGS. 4 through 6 illustrate an integrated cleaning process including a metal oxide removal and a de-ionized water cleaning process, which integrated cleaning process is performed in an integrated cleaning station;

FIG. 7 illustrates a schematic cross-sectional view of the first package component after the integrated cleaning process is performed;

FIG. 8 illustrates the cross-sectional view of a pre-bonding process for pre-bonding the first and the second package components; and

FIG. 9 illustrates a process flow for bonding package components and a hybrid bonding system for performing the bonding in accordance with exemplary embodiments.

DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

The making and using of the embodiments of the disclosure are discussed in detail below. It should be appreciated, however, that the embodiments provide many applicable concepts that can be embodied in a wide variety of specific contexts. The specific embodiments discussed are illustrative, and do not limit the scope of the disclosure.

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A method for bonding package components and the apparatus for performing the bonding are provided in accordance with various exemplary embodiments. The intermediate stages of the bonding process are illustrated. The variations of the apparatus and bonding methods in accordance with embodiments are discussed. Throughout the various views and illustrative embodiments, like reference numbers are used to designate like elements.

FIGS. 1 through 8 illustrate cross-sectional views of intermediate stages in a bonding process in accordance with exemplary embodiments of the present disclosure. The process steps may be performed using the integrated hybrid bonding system 300, which is schematically shown in the process flow in FIG. 9. The process flow in accordance with the embodiments is briefly described herein, and the details of the process flow and integrated hybrid bonding system 300 are discussed referring to the process steps shown in FIGS. 1 through 8.

Referring to FIG. 9, the package components that are to be bonded (for example, package components 100 and 200 in FIGS. 1 and 2, respectively) are loaded into integrated hybrid bonding system 300 through loading station 302. Integrated hybrid bonding system 300 may be located in a controlled environment, for example, filled with clean air or nitrogen. Alternatively, integrated hybrid bonding system 300 is located in open air. Next, a surface treatment/activation is performed on the surfaces of the package components, wherein the surface treatment is performed in surface treatment station 304. In the surface treatment, the exposed surfaces of the dielectric materials in the package components are activated. An integrated cleaning step is then performed on the package components to remove metal oxides, chemicals, particles, or other undesirable substances from the surfaces of the package components. Integrated cleaning station 306 is configured to perform the integrated cleaning step in accordance with some embodiments.

A pre-bonding is then performed to bond the package components together. The pre-bonding is performed in pre-bonding station 308. After the pre-bonding, the package components are bonded to each other. The bonded package components may then be unloaded from integrated hybrid bonding system 300 through unloading station 310, and transferred into annealing station 312. The bonding strength is then enhanced through a thermal annealing, which is held in thermal annealing station 312.

In the integrated hybrid bonding system 300, a plurality of transferring tools 314 are used to transfer the package components between stations 304, 306, and 308, so that stations 304, 306, and 308 may be integrated together as an integrated system. Transferring tools 314 may include robot arms (not shown), transferring guides (not shown), and/or the like, which are used to automatically transfer the package components from one station to another, so that the bonding process may be automated. After the bonding process is finished, the bonded package components are unloaded from integrated hybrid bonding system 300 using unloading station 310, which may include robot arms, for example. In addition, some or all of stations 304, 306, and 308 and transferring tools 314 may be connected to a central control unit 316, which controls, and coordinates, the operations of stations 304, 306, and 308 and transferring tools 314.

A brief hybrid bonding process is discussed herein referring to FIGS. 1 through 8. Referring to FIG. 1, package component 100 is illustrated. Package component 100 may comprise a device wafer, a package substrate strip, an interposer wafer, or the like. In the embodiments in which

package component **100** comprise a device wafer, package component **100** may include semiconductor substrate **102**, which may be, for example, a silicon substrate, although other semiconductor substrates are also usable. Active devices **104** may be formed on a surface of substrate **102**, and may include, for example, transistors. Metal lines and vias **106** are formed in dielectric layers **108**, which may be low-k dielectric layers in some embodiments. The low-k dielectric layers **108** may have dielectric constants (k values) lower than about 3.5, lower than about 3.0, or lower than about 2.5, for example. Dielectric layers **108** may also comprise non-low-k dielectric materials having dielectric constants (k values) greater than 3.9. Metal lines and vias **106** may comprise copper, aluminum, nickel, tungsten, or alloys thereof. Metal lines and vias **106** interconnect active devices **104**, and may connect active devices **104** to the overlying metal pads **112**.

In alternative embodiments, package component **100** is an interposer wafer, which is free from active devices therein. Package component **100** may, or may not, include passive devices (not shown) such as resistors, capacitors, inductors, transformers, and the like in accordance with some embodiments.

In yet alternative embodiments, package component **100** is a package substrate strip. In some embodiments, package component **100** includes laminate package substrates, wherein conductive traces **106** (which are schematically illustrated) are embedded in laminate dielectric layers **108**. In alternative embodiments, package components **100** are build-up package substrates, which comprise cores (not shown) and conductive traces (represented by **106**) built on opposite sides of the cores.

In each of the embodiments wherein package component **100** is a device wafer, an interposer wafer, a package substrate strip, or the like, surface dielectric layer **110** is formed at the surface of package component **100**. In some embodiments, surface dielectric layer **110** is an oxide layer, which may comprise silicon oxide, SiON, SiN, or the like. Metal pads **112** are formed in surface dielectric layer **110**, and may be electrically coupled to active devices **104** through metal lines and vias **106**. Metal pads **112** may also be formed of copper, aluminum, nickel, tungsten, or alloys thereof. The top surface of surface dielectric layer **110** and the top surfaces of metal pads **112** are substantially level with each other. FIG. 1 also illustrates metal oxide regions **114** formed on the surfaces of metal pads **112**. Metal oxide regions **114** may be the native oxide regions that are formed due to the exposure of metal pads **112** to open air.

In the embodiments wherein package component **100** is a device wafer, surface dielectric layer **110** and metal pads **112**, which are used for the subsequent bonding, may be on the front side (the side with active devices **104**) or the back side of substrate **102**, although FIG. 1 illustrates that surface dielectric layer **110** and metal pads **112** are on the front side of substrate **102**.

FIG. 2 illustrates package component **200**, which is to be bonded to package component **100**. Package component **200** may also be selected from a device wafer, an interposer wafer, a package substrate, and the like. In the illustrated FIG. 2, package component **200** includes substrate **202**, active devices **204**, dielectric layers **208**, metal lines and vias **206** in dielectric layers **208**, surface dielectric layer **210**, and metal pads **212**. Package component **200** may have a structure similar to what is described for package component **100**, and the details are not repeated herein. The materials of the features in package component **200** may be found referring to the like features in package component **100**, with the like

features in package component **100** starting with number “1,” which features correspond to the features in package component **200** and having reference numerals starting with number “2.”

Next, referring to FIG. 3, package component **100** is loaded into surface treatment station **304**, which is a part of integrated hybrid bonding system **300** in FIG. 9. The loading may be performed using loading station **302** as described regarding FIG. 9. Referring to FIG. 3, a surface treatment (symbolized by arrows **320**) is performed on the surface of package component **100**. In some embodiments, the surface treatment includes a plasma treatment.

The plasma treatment may be performed in a vacuum environment (a vacuum chamber), for example, which is a part of the surface treatment station **304** (FIGS. 3 and 9). The process gas used for generating the plasma may be a hydrogen-containing gas, which includes a first combined gas of hydrogen (H_2) and argon (Ar), a second combined gas of H_2 and nitrogen (N_2), or a third combined gas of H_2 and helium (He). In some exemplary embodiments, the flow rate ratio of H_2 in the first, the second, or the third combined gas, whichever is used in the plasma treatment, may be between about 4 percent and about 5 percent. Through the treatment, the number of OH groups at the surface of surface dielectric layer **110** is increased, which is beneficial for forming strong fusion bonds. Furthermore, the hydrogen helps reduce the metal oxide **114** on the surfaces of metal pads **112** back to metal. The plasma treatment may also be performed using pure or substantially pure H_2 , Ar, or N_2 as the process gas, which treats the surfaces of metal pads **112** and surface dielectric layer **110** through reduction and/or bombardment. The plasma used in the treatment may be low-power plasma, with the power for generating the plasma between about 10 Watts and about 2,000 Watts. Using surface treatment station **304** in FIG. 3, package component **200** is also treated, which treatment is essentially the same as the treatment of package component **100**.

Next, referring to FIG. 4, package component **100** is transferred to integrated cleaning station **306**, and a metal oxide removal and a De-Ionized (DI) water cleaning are performed on package component **100**. The integrated cleaning station **306** includes chamber **402**, which may be sealed to confine the chemical vapors, which chemical vapors are evaporated from the chemicals used in the cleaning processes that are performed inside chamber **402**. Integrated cleaning station **306** includes a plurality of containers **404**, **406**, and **408** therein. In some embodiments, the plurality of containers is disposed by placing smaller containers inside larger containers. For example, container **404** is smaller than, and is placed inside, container **406**, and container **406** is smaller than, and is placed inside, container **408**. Furthermore, the sidewalls of the outer containers are higher than the sidewalls of the respective inner containers therein. For example, container **408** has the highest sidewalls, while container **404** has the lowest sidewalls. Containers **404**, **406**, and **408** are connected to outlets **414**, **416**, and **418**, respectively, so that the chemical solutions collected by the containers may be extracted out of chamber **402**, and may be collected separately in accordance with the types of the collected chemical solutions. In some exemplary embodiments, containers **404**, **406**, and **408** are used to collect used acid solution, used alkaline solution, and used DI water, respectively. In alternative embodiments, the functions of containers **404**, **406**, and **408** may be switched.

Integrated cleaning station **306** also includes a plurality of storages, for example, **424**, **426**, and **428**. The plurality of storages is used to store the chemicals/solutions that are used

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in the metal oxide removal and the DI water cleaning. For example, **424**, **426**, and **428** may store an acidic solution, an alkaline solution, and DI water, respectively. Integrated cleaning station **306** is configured to mix the chemicals and the DI water, and dispose the chemicals, either mixed or not mixed, to nozzle **430**, which is used to dispense the chemical solution to the package component (such as package component **100** in FIGS. **5A**, **5B**, and **6**) that is to be cleaned.

Retractable wafer support **432** is located in chamber **402**. Retractable wafer support **432** may extend or retract as desired to different levels during the integrated cleaning process. Hence, retractable wafer support **432** may raise package component **100**, as shown in FIG. **6**, or lower package component **100**, as shown in FIG. **5B**. In some embodiments, air outlets **434** are disposed in retractable wafer support **432**, and are used to blow air **440** to the back side of package component **100**, as will be discussed referring to FIGS. **5A**, **5B**, and **6**.

Integrated cleaning station **306** also includes ultrasonic generator **436**, which is used to generate ultrasound. The ultrasound is used in the cleaning process, for example, when DI water is disposed on package component **100**. As also shown in FIG. **4**, chamber **402** includes door **438**, which is opened to allow package component **100** to be transported into and out of chamber **402**.

Referring to FIG. **5A**, after package component **100** is transported into chamber **402**, door **438** is closed. During the time period that door **438** is opened, as shown in FIG. **4**, and during the time period door **438** is closed, as shown in FIGS. **5A**, **5B**, and **6**, a negative pressure is generated in chamber **402**, for example, by suck air **439** into chamber **402**, and then evacuate the air through an outlet (not shown). With the negative pressure, which means that the pressure inside chamber **402** is lower than the pressure (for example, one atmosphere) outside chamber **402**, air always flows into, not out of, chamber **402** (except through the outlet). Hence, the chemical vapors in chamber **402** will not escape to pollute the package components and other tools in integrated cleaning station **306**.

FIG. **5A** illustrates the metal oxide removal using an alkaline solution, through which oxide regions **114** (FIG. **1**) are removed. An alkaline solution such as Ammonium Hydroxide (NH_4OH) solution is disposed on package component **100**. During the oxide removal, package component **100** is rotated to spin off the used alkaline solution. Through the reaction of the alkaline solution with metal oxide regions **114**, metal oxide regions **114** are removed. In addition, some loose particles and undesirable substances on the surfaces of metal pads **112** and surface dielectric layer **110** are also removed. Retractable wafer support **432** may adjust the height of package component **100** to a level higher than the top edges of container **404**, and lower than the top edges of container **406**. The alkaline solution spun off from package component **100** may thus be spun off to the sidewalls of container **406**, and evacuated out of chamber **402** through outlet **416**. During the metal oxide removal using the alkaline solution, ultrasonic generator **436** may, or may not, supply ultrasound to package component **100**.

FIG. **5B** illustrates the metal oxide removal using an acidic solution, through which oxide regions **114** (FIG. **1**) may also be removed. During the oxide removal, an acidic solution such as formic acid (HCOOH) solution is disposed on package component **100**. Package component **100** is rotated to spin off the used acidic solution. Through the use of the acidic solution, the metal oxide regions **114** on the surfaces of metal pads **112** are removed. Some particles and undesirable substances on the surface of metal pads **112** and

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surface dielectric layer **110** are also removed. Retractable wafer support **432** may lower package component **100** to a level lower than the top edges of container **404**. The acidic solution spun off from package component **100** may thus be spun off to the sidewalls of container **404**, and evacuated out of chamber **402** through outlet **414**. During the metal oxide removal using the acidic solution, ultrasonic generator **436** may, or may not, supply ultrasound to package component **100**.

In accordance with some embodiments, one or both of the alkaline cleaning and/or acid cleaning is performed on package component **100** before it is pre-bonded. After the alkaline cleaning and/or the acid cleaning, a DI water cleaning is performed, as shown in FIG. **6**, during which DI water is dispensed on the respective package component **100**. Package component **100** is also rotated to spin off the used DI water. Through the use of DI water, the residue of the acidic solution and/or the alkaline solution is removed. During the DI water clean, retractable wafer support **432** may raise package component **100** to a level higher than the top edges of container **406**, and lower than the top edges of container **408**. The DI water spun off from package component **100** may thus be spun off to the sidewalls of container **408**, and evacuated out of chamber **402** through outlet **418**. During the cleaning using DI water, ultrasonic generator **436** may, or may not, supply ultrasound to package component **100**.

During the alkaline cleaning, the acid cleaning, and possibly the DI water cleaning, air, clean air, nitrogen, or other type of gas, which are represented by arrows **440**, may be blown out of outlets **434** (FIGS. **5A**, **5B**, and **6**). This prevents the acidic solution and the alkaline solution from flowing to the backside of package component **100** to contaminate the backside.

Package component **200** is also cleaned using essentially the same process as shown in FIGS. **4** through **6**. After the integrated cleaning, the oxide regions on both package components **100** and **200** are removed. FIG. **7** illustrates package component **100**, wherein metal pads **112** no longer have metal oxide regions thereon.

Next, as shown in FIG. **8**, package components **100** and **200** are transferred into pre-bonding station **308** (also refer to FIG. **9**). Package components **100** and **200** are aligned, with bond pads **112** of package component **100** being aligned to bond pads **212** of package component **200**. The alignment may be performed in pre-bonding station **308** (which is an alignment and pre-bonding station in these embodiments), although it may also be performed in a separate alignment station. After the alignment, package components **100** and **200** are pressed against each other. At the time the pre-bonding is performed, substantially no oxide is re-grown on the surface of metal pads **112** and **212**. This is due to the fact that the oxide regions are removed in the integrated cleaning station **306**, which is a part of the hybrid bonding system. Accordingly, the time period between the removal of the oxide and the pre-bonding is short enough, and hence substantially no oxide is grown. In addition, the environment of hybrid bonding system **300** (FIG. **9**) may be controlled, which includes, for example, using cleaned air or nitrogen (or other inert gases) to fill hybrid bonding system **300**, removing moisture from the air in hybrid bonding system **300**, etc. As shown in FIG. **8**, during the pre-bonding, pressing force **326** is applied to press package components **100** and **200** against each other. Pressing force **326** may be lower than about 5 Newton per die in some exemplary embodiments, although a greater or a smaller force may also be used. The pre-bonding may be

performed at the room temperature (for example, between about 21° C. and about 25° C.), although higher temperatures may be used. The bonding time may be shorter than about 1 minute, for example.

After the pre-bonding, surface dielectric layer **110** and **210** are bonded to each other. The bonding strength, however, needs to be improved in a subsequent annealing step. The bonded package components **100** and **200** in combination are referred to as bonded pair **324** hereinafter. Bonded pair **324** is unloaded out of pre-bonding station **308** and integrated cleaning station **306** (FIG. 9), and is transferred to annealing station **312** (FIG. 9) for annealing.

Referring to FIG. 9, in annealing station **312**, the bonded pair **324** is annealed at a temperature between about 300° C. and about 400° C., for example. The annealing may be performed for a period of time between about 1 hour and 2 hours in some exemplary embodiments. When temperature rises, the OH bonds in oxide layers **110** and **210** (FIG. 8) break to form strong Si—O—Si bonds, and hence package components **100** and **200** are bonded to each other through fusion bonds. In addition, during the annealing, the copper in metal pads **112** and **212** diffuse to each other, so that metal-to-metal bonds are also formed. Hence, the resulting bonds between package components **100** and **200** are hybrid bonds.

In the embodiments of the present disclosure, by integrating the integrated cleaning station into the hybrid bonding system, the oxides on the surfaces of metal bonds are removed. Experiments have shown that in conventional bonding processes in which the DI water clean is performed, and no oxide removal is performed in the respective hybrid bonding station **300**, a resulting bond structure has a clearly visible interface, indicating the inferior inter-diffusion of copper atoms. The bond quality is hence low. As a comparison, by removing the oxide in hybrid bonding system, there is substantially no metal oxide re-grown when the bonding is performed. The resulting bond structure has no visible interface, indicating the high-quality inter-diffusion of copper atoms has occurred, and quality of bonds is improved.

In accordance with some embodiments, a method includes performing a plasma activation on a surface of a first package component, removing oxide regions from surfaces of metal pads of the first package component, and performing a pre-bonding to bond the first package component to a second package component.

In accordance with other embodiments, a hybrid bonding system includes a plasma treatment chamber configured to perform a plasma cleaning on a package component, and an integrated cleaning station. The integrated cleaning station includes a chamber, and a plurality of storages outside of the chamber. The plurality of storages comprises a first storage storing one of an acidic solution and an alkaline solution therein and a second storage storing deionized water therein. The integrated cleaning station further includes a nozzle in the chamber and connected to the plurality of storages, and a retractable wafer support configured to hold the package component thereon. The hybrid bonding system further includes an alignment and pre-bonding station configured to align and bonding the package component with an additional package component.

Although the embodiments and their advantages have been described in detail, it should be understood that various changes, substitutions and alterations can be made herein without departing from the spirit and scope of the embodiments as defined by the appended claims. Moreover, the scope of the present application is not intended to be limited

to the particular embodiments of the process, machine, manufacture, and composition of matter, means, methods and steps described in the specification. As one of ordinary skill in the art will readily appreciate from the disclosure, processes, machines, manufacture, compositions of matter, means, methods, or steps, presently existing or later to be developed, that perform substantially the same function or achieve substantially the same result as the corresponding embodiments described herein may be utilized according to the disclosure. Accordingly, the appended claims are intended to include within their scope such processes, machines, manufacture, compositions of matter, means, methods, or steps. In addition, each claim constitutes a separate embodiment, and the combination of various claims and embodiments are within the scope of the disclosure.

What is claimed is:

1. A method comprising:

performing a plasma activation on a surface of a first package component, wherein the first package component comprises oxide regions on surfaces of first metal pads, with the oxide regions comprising an oxide of a metal, and wherein portions of the oxide regions of the first package component are reduced by the plasma activation;

removing remaining portions of the oxide regions from the surfaces of the first metal pads;

performing a pre-bonding to bond the first package component to a second package component; and

after the pre-bonding, annealing the first package component and the second package component, wherein after the annealing, the first metal pads are bonded to second metal pads of the second package component through direct metal-to-metal bonding, and a first surface dielectric layer of the first package component is bonded to a second surface dielectric layer of the second package component through fusion bonding.

2. The method of claim 1, wherein the step of removing the oxide regions is performed in an integrated cleaning station configured to perform at least one of acid oxide removal and alkaline removal, and wherein the method further comprises performing a de-ionized water cleaning on the first package component in the integrated cleaning station.

3. The method of claim 1 further comprising, during the step of removing the oxide regions, forming a negative pressure in a chamber for performing the step of removing the oxide regions, wherein a surface of the oxide regions is exposed to the negative pressure.

4. The method of claim 1, wherein the oxide regions are removed using formic acid (HCOOH) or Ammonium Hydroxide (NH₄OH).

5. A method comprising:

performing a plasma activation on a surface of a first package component;

transporting the first package component into an integrated cleaning station;

adjusting a height of the first package component to a first level;

removing oxide regions from surfaces of first metal pads of the first package component in the integrated cleaning station, wherein the oxide regions are removed when the first package component is at the first level, and wherein a chemical used in the removing the oxide regions is collected by a first container;

adjusting the height of the first package component to a second level different from the first level;

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performing a De-Ionized (DI) water cleaning on the first package component in the integrated cleaning station, wherein the DI water cleaning is performed when the first package component is at the second level, and wherein the DI water used in the DI water cleaning is collected by a second container different from the first container;

performing a pre-bonding to bond the first package component to a second package component to form a bonded pair, wherein the pre-bonding is performed at a temperature close to room temperature; and

after the pre-bonding, annealing the bonded pair, wherein after the annealing, first metal pads of the first package component are bonded to second metal pads of the second package component through direct metal-to-metal bonding, and a first surface dielectric layer of the first package component is bonded to a second surface dielectric layer of the second package component through fusion bonding.

6. The method of claim 5, wherein the oxide regions are removed by an acidic solution.

7. The method of claim 5, wherein the oxide regions are removed by an alkaline solution.

8. The method of claim 5, wherein the step of removing the oxide regions is performed after the step of performing the plasma activation, and wherein substantially no native oxide is grown on the surface of the first metal pads when the pre-bonding is performed.

9. The method of claim 5, wherein the step of removing the oxide regions is performed in an integrated cleaning station configured to perform steps of:

performing acid oxide removal steps to remove the oxide regions;

performing alkaline oxide removal steps to remove the oxide regions; and

performing the DI water cleaning.

10. The method of claim 5, wherein the step of removing the oxide regions is performed in a chamber having a negative pressure, wherein a surface of the oxide regions is exposed to the negative pressure.

11. The method of claim 5, wherein the oxide regions are removed using formic acid (HCOOH).

12. The method of claim 5, wherein some portions of the oxide regions are reduced to metal by the plasma activation.

13. A method comprising:

in a controlled environment, transporting a first package component into an integrated cleaning station, wherein the controlled environment is filled with clean air or an inert gas;

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removing oxide regions from surfaces of first metal pads of the first package component in the integrated cleaning station, wherein a chemical used for removing oxide regions is collected by a first container;

performing a De-Ionized (DI) water cleaning on the first package component in the integrated cleaning station, wherein a DI water used in the DI water cleaning is collected by a second container different from the first container, with both the first container and the second container being in the integrated cleaning station; and in the controlled environment, transporting the first package component out of the integrated cleaning station.

14. The method of claim 13 further comprising:

performing a pre-bonding to bond the first package component to a second package component to form a bonded pair, wherein the pre-bonding is performed in a pre-bonding station, and the pre-bonding station is located in the controlled environment.

15. The method of claim 13 further comprising removing moisture from the controlled environment.

16. The method of claim 13 further comprising adjusting the first package component to a first height to remove the oxide regions, and adjusting the first package component to a second height different from the first height to perform the DI water cleaning.

17. The method of claim 2 further comprising:

adjusting a height of the first package component to a first level, and removing the remaining portions of the oxide regions using the one of the acid oxide removal and alkaline removal when the first package component is at the first level, and wherein a chemical used in the step of removing the remaining portions of the oxide regions is collected by a first container; and

adjusting the height of the first package component to a second level different from the first level; and

performing a De-Ionized (DI) water cleaning on the first package component in the integrated cleaning station, with the DI water cleaning performed when the first package component is at the second level, wherein the DI water used in the DI water cleaning is collected by a second container different from the first container.

18. The method of claim 5, wherein a top edge of the first container and a top edge of the second container are at different heights, and the chemical used in the removing the oxide regions and the DI water are spun off into the first container and the second container, respectively.

19. The method of claim 1, wherein the portions of the oxide regions of the first package component are reduced by the plasma activation back to metal.

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